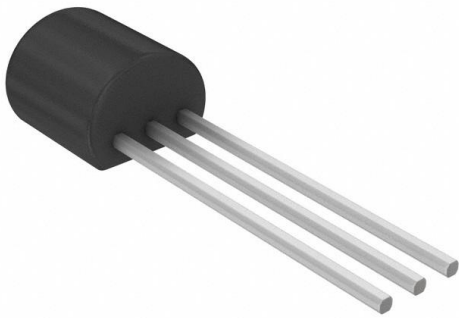


ZTX653STOA Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	ZTX653STOA-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	ZTX653STOA
Description	TRANS NPN 100V 2A E-LINE
Detailed Description	Bipolar (BJT) Transistor NPN 100 V 2 A 175MHz 1 W Through Hole E-Line (TO-92 compatible)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

ZTX653STOA

Series:

-

Transistor Type:

NPN

Voltage - Collector Emitter Breakdown (Max):

100 V

Current - Collector Cutoff (Max):

100nA (ICBO)

Power - Max:

1 W

Operating Temperature:

-55°C ~ 200°C (TJ)

Package / Case:

E-Line-3, Formed Leads

Base Product Number:

ZTX653

Manufacturer:

Diodes Incorporated

Product Status:

Obsolete

Current - Collector (Ic) (Max):

2 A

Vce Saturation (Max) @ Ib, Ic:

500mV @ 200mA, 2A

DC Current Gain (hFE) (Min) @ Ic, Vce:

-

Frequency - Transition:

175MHz

Mounting Type:

Through Hole

Supplier Device Package:

E-Line (TO-92 compatible)

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0075

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

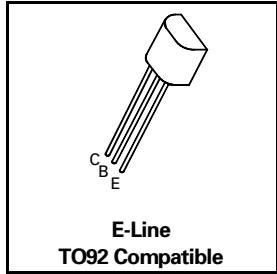
NPN SILICON PLANAR MEDIUM POWER TRANSISTORS



ISSUE 2 – JULY 94

FEATURES

- * 100 Volt V_{CE0}
- * 2 Amp continuous current
- * Low saturation voltage
- * $P_{tot}=1$ Watt



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	ZTX652	ZTX653	UNIT
Collector-Base Voltage	V_{CBO}	100	120	V
Collector-Emitter Voltage	V_{CEO}	80	100	V
Emitter-Base Voltage	V_{EBO}	5		V
Peak Pulse Current	I_{CM}	6		A
Continuous Collector Current	I_C	2		A
Power Dissipation at $T_{amb}=25^{\circ}C$ derate above $25^{\circ}C$	P_{tot}	1	5.7	W mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200		$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	ZTX652			ZTX653			UNIT	CONDITIONS.
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	100			120			V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80			100			V	$I_C=10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			5			V	$I_E=100\mu A$
Collector Cut-Off Current	I_{CBO}			0.1 10			0.1 10	μA	$V_{CB}=80V$ $V_{CB}=100V$ $V_{CB}=80V, T_{amb}=100^{\circ}C$ $V_{CB}=100V, T_{amb}=100^{\circ}C$
Emitter Cut-Off Current	I_{EBO}			0.1			0.1	μA	$V_{EB}=4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.13 0.23	0.3 0.5			0.13 0.23 0.5	V	$I_C=1A, I_B=100mA^*$ $I_C=2A, I_B=200mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		0.9	1.25			0.9 1.25	V	$I_C=1A, I_B=100mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		0.8	1			0.8 1	V	$I_C=1A, V_{CE}=2V^*$

ZTX6535T0A Diodes Incorporated TRANS NPN 100V 2A E-LINE

ZTX652 ZTX653

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

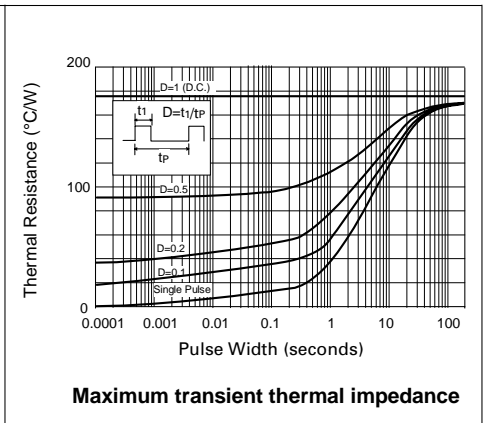
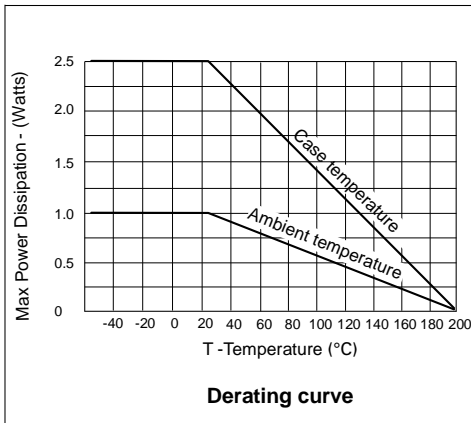
PARAMETER	SYMBOL	ZTX652			ZTX653			UNIT	CONDITIONS.
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Transition Frequency	f_T	140	175		140	175		MHz	$I_C=100\text{mA}$, $V_{CE}=5\text{V}$ $f=100\text{MHz}$
Switching Times	t_{on}		80			80		ns	$I_C=500\text{mA}$, $V_{CC}=10\text{V}$ $I_{B1}=I_{B2}=50\text{mA}$
	t_{off}		1200			1200		ns	
Output Capacitance	C_{obo}			30			30	pF	$V_{CB}=10\text{V}$ $f=1\text{MHz}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

THERMAL CHARACTERISTICS

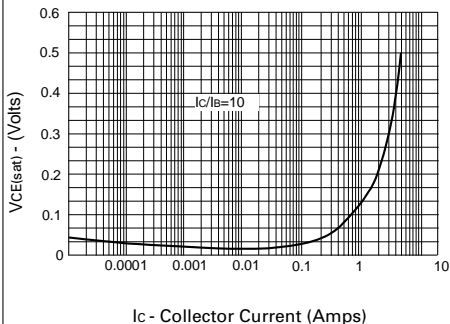
PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient ₁	$R_{th(j-amb)1}$	175	$^{\circ}\text{C/W}$
Junction to Ambient ₂	$R_{th(j-amb)2}^{\dagger}$	116	$^{\circ}\text{C/W}$
Junction to Case	$R_{th(j-case)}$	70	$^{\circ}\text{C/W}$

\dagger Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.

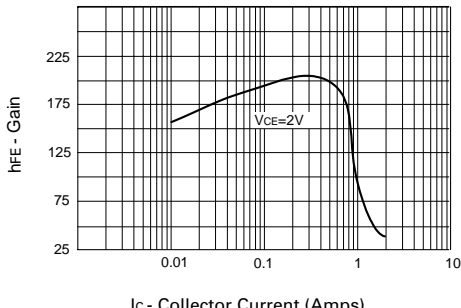


ZTX652 ZTX653

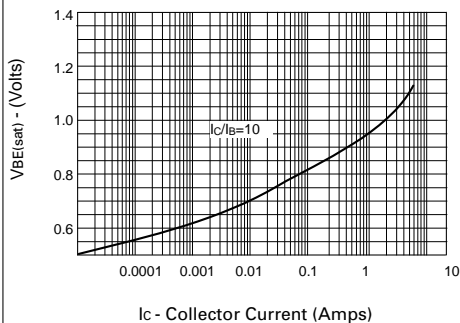
TYPICAL CHARACTERISTICS



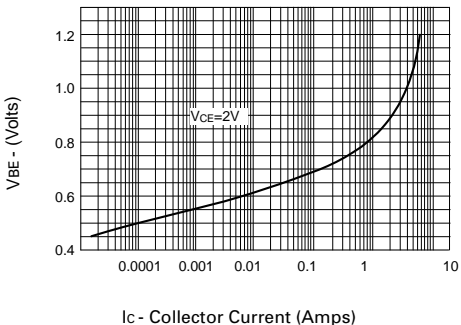
$V_{CE(sat)}$ v I_C



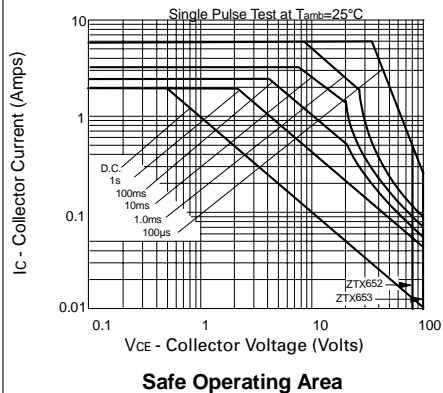
h_{FE} v I_C



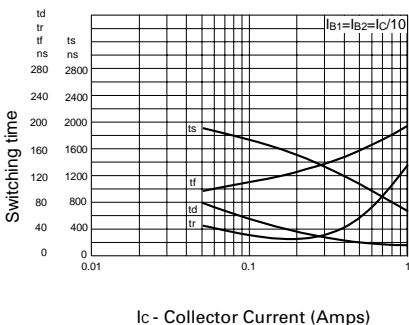
$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area



Switching Speeds

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